

N-channel 40 V, 3.0 mΩ standard level MOSFET in LFPAK56 10 May 2018 Product data sheet

1. General description

Automotive qualified N-channel MOSFET using the latest Trench 9 low ohmic superjunction technology, housed in a robust LFPAK56 package. This product has been fully designed and qualified to meet AEC-Q101 requirements delivering high performance and endurance.

2. Features and benefits

- Fully automotive qualified to AEC-Q101:
 - 175 °C rating suitable for thermally demanding environments
- Trench 9 Superjunction technology:
 - Reduced cell pitch enables enhanced power density and efficiency with lower $\mathsf{R}_{\mathsf{DSon}}$ in same footprint
 - Improved SOA and avalanche capability compared to standard TrenchMOS
 - Tight V_{GS(th)} limits enable easy paralleling of MOSFETs
- LFPAK Gull Wing leads:
 - High Board Level Reliability absorbing mechanical stress during thermal cycling, unlike traditional QFN packages
 - · Visual (AOI) soldering inspection, no need for expensive x-ray equipment
 - Easy solder wetting for good mechanical solder joint
- LFPAK copper clip technology:
 - Improved reliability, with reduced R_{th} and R_{DSon}
 - · Increases maximum current capability and improved current spreading

3. Applications

- 12 V automotive systems
- Motors, lamps and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching



4. Quick reference data

Table 1. Quic	k reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C	-	-	40	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C	-	-	120	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>	-	-	172	W
Static chara	cteristics	·				·
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 10	1.8	2.55	3	mΩ
Dynamic cha	aracteristics					
Q _{GD}	gate-drain charge	I_D = 25 A; V_{DS} = 32 V; V_{GS} = 10 V; Fig. 12; Fig. 13	-	6.3	15.8	nC
Source-drain	n diode			-		
Q _r	recovered charge	$I_{\rm S}$ = 25 A; dI_{S}/dt = -100 A/µs; V_{GS} = 0 V; V_{\rm DS} = 20 V	-	19.5	-	nC
S	softness factor	$I_{S} = 25 \text{ A}; \text{ dI}_{S}/\text{dt} = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$ $\text{V}_{DS} = 20 \text{ V}; \text{ T}_{j} = 25 \text{ °C}; \text{ Fig. 16}$	-	0.8	-	

5. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D
2	S	source		
3	S	source	a	G L F
4	G	gate		mbb076 S
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

6. Ordering information

Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
BUK7Y3R0-40H	LFPAK56; Power-SO8	plastic, single-ended surface-mounted package; 4 terminals	SOT669				

7. Marking

Table 4.	Marking	codes
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Type number	Marking code
BUK7Y3R0-40H	73H040

Product data sheet

8. Limiting values

Table 5. Limiting values

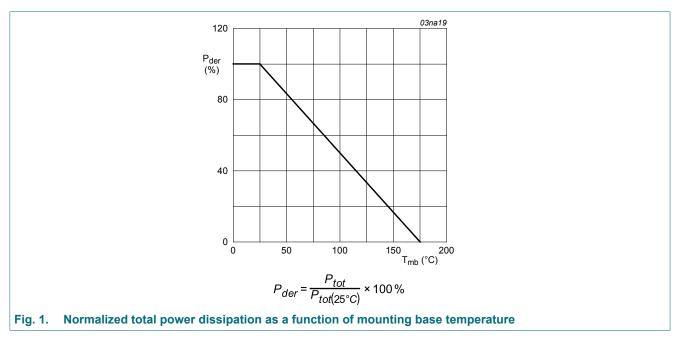
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	40	V
V _{GS}	gate-source voltage	DC; T _j ≤ 175 °C		-10	20	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	172	W
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C		-	120	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$; Fig. 2		-	600	A
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drai	n diode			•		
I _S	source current	T _{mb} = 25 °C	[1]	-	120	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	600	А
Avalanche r	uggedness			•		
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	$\label{eq:loss} \begin{array}{l} I_D = 120 \text{ A}; V_{sup} \leq 40 \text{ V}; \text{R}_{GS} = 50 \Omega; \\ $	[2] [3]	-	50	mJ

[1] 120A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

[2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

[3] Refer to application note AN10273 for further information.

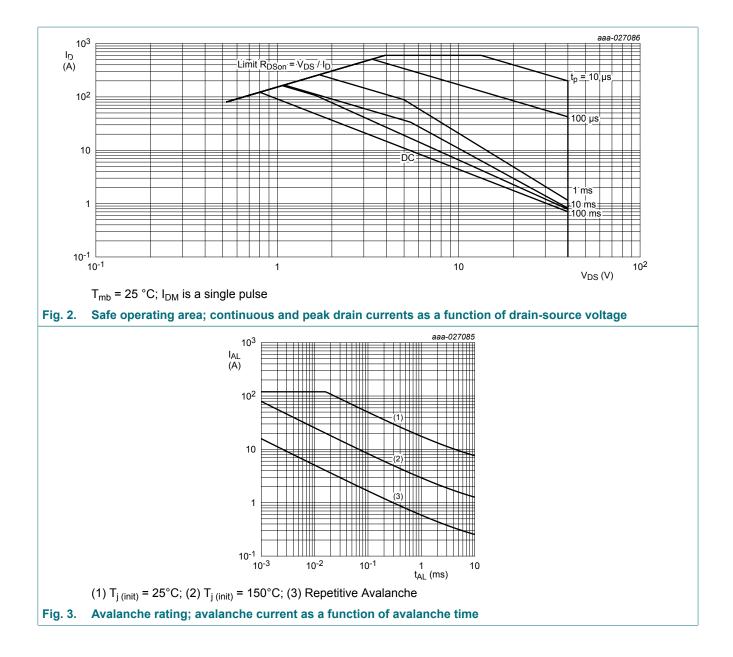


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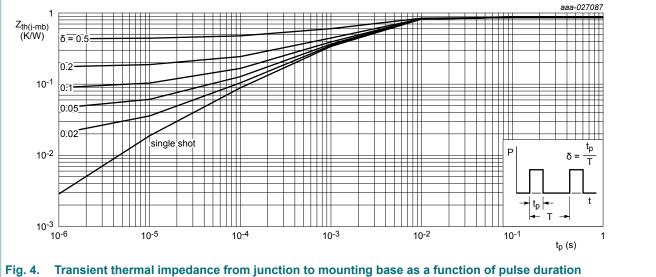
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9. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 4	-	-	0.77	0.87	K/W



10. Characteristics

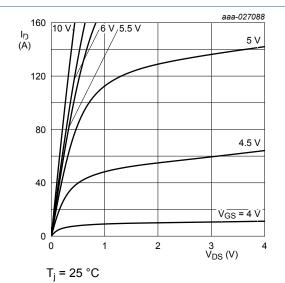
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	40	43	-	V
	breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = -40 °C	-	40.5	-	V
		I _D = 250 μA; V _{GS} = 0 V; T _j = -55 °C	36	40	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = 25 \text{ °C}; Fig. 8;$ Fig. 9	2.4	3	3.6	V
		I _D = 1 mA; V _{DS} =V _{GS} ; T _j = -55 °C; <u>Fig. 8</u>	-	-	4.3	V
		I _D = 1 mA; V _{DS} =V _{GS} ; T _j = 175 °C; <u>Fig. 8</u>	1	-	-	V
I _{DSS}	drain leakage current	V _{DS} = 40 V; V _{GS} = 0 V; T _j = 25 °C	-	0.06	1	μA
		V _{DS} = 16 V; V _{GS} = 0 V; T _j = 125 °C	-	0.8	10	μA
		V _{DS} = 40 V; V _{GS} = 0 V; T _j = 175 °C	-	80	500	μA
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 10	1.8	2.55	3	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 105 °C; Fig. 11	2.5	3.6	4.8	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 125 °C; Fig. 11	2.8	4	5.3	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; Fig. 11	3.5	5	6.5	mΩ
R _G	gate resistance	f = 1 MHz; T _j = 25 °C	0.34	0.85	2.12	Ω
Dynamic ch	naracteristics	· · ·				
Q _{G(tot)}	total gate charge	I _D = 25 A; V _{DS} = 32 V; V _{GS} = 10 V;	-	34	59	nC
Q _{GS}	gate-source charge	Fig. 12; Fig. 13	-	9.8	15	nC
Q _{GD}	gate-drain charge	1	-	6.3	15.8	nC
C _{iss}	input capacitance	V _{DS} = 25 V; V _{GS} = 0 V; f = 1 MHz;	-	2417	5449	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 14</u>	-	688	1377	pF
C _{rss}	reverse transfer capacitance		-	108	415	pF
t _{d(on)}	turn-on delay time	V_{DS} = 30 V; R _L = 1.2 Ω; V _{GS} = 10 V;	-	10	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega$	-	8.1	-	ns
t _{d(off)}	turn-off delay time	1	-	21.4	-	ns
t _f	fall time	1	-	10	-	ns
Source-drai	in diode		I	_1	-1	
V _{SD}	source-drain voltage	I _S = 25 A; V _{GS} = 0 V; T _i = 25 °C; <u>Fig. 15</u>	-	0.8	1.2	V

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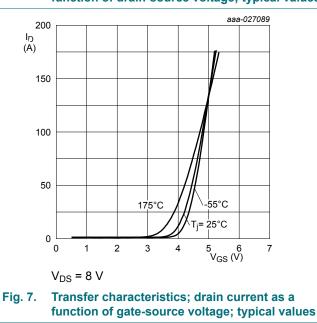
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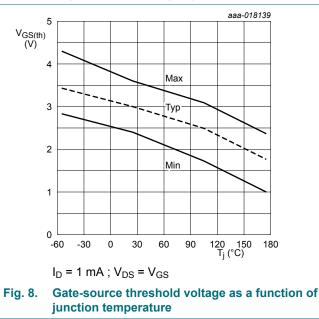
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
t _{rr}	reverse recovery time	$I_{S} = 25 \text{ A}; \text{ d}_{S}/\text{d}t = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V}; \\ \text{V}_{DS} = 20 \text{ V}$	-	27	-	ns
Qr	recovered charge		-	19.5	-	nC
S	$\label{eq:softness factor} \begin{array}{l} I_{S} = 25 \; A; \; dI_{S}/dt = -100 \; A/\mu s; \; V_{GS} = 0 \; V; \\ V_{DS} = 20 \; V; \; T_{j} = 25 \; ^{\circ}\text{C}; \; \underline{Fig. 16} \\ \\ \hline I_{S} = 25 \; A; \; dI_{S}/dt = -500 \; A/\mu s; \; V_{GS} = 0 \; V; \\ V_{DS} = 20 \; V; \; T_{j} = 25 \; ^{\circ}\text{C}; \; \underline{Fig. 16} \end{array}$	-	0.8	-		
		$I_{S} = 25 \text{ A}; \text{ dI}_{S}/\text{dt} = -500 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V}; \\ \text{V}_{DS} = 20 \text{ V}; \text{ T}_{j} = 25 ^{\circ}\text{C}; \text{ Fig. 16}$	-	0.7	-	







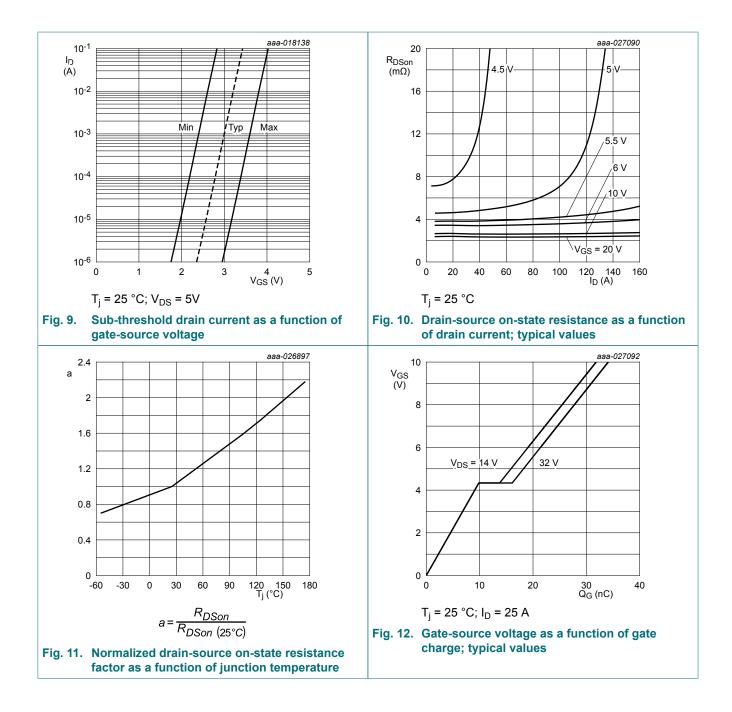




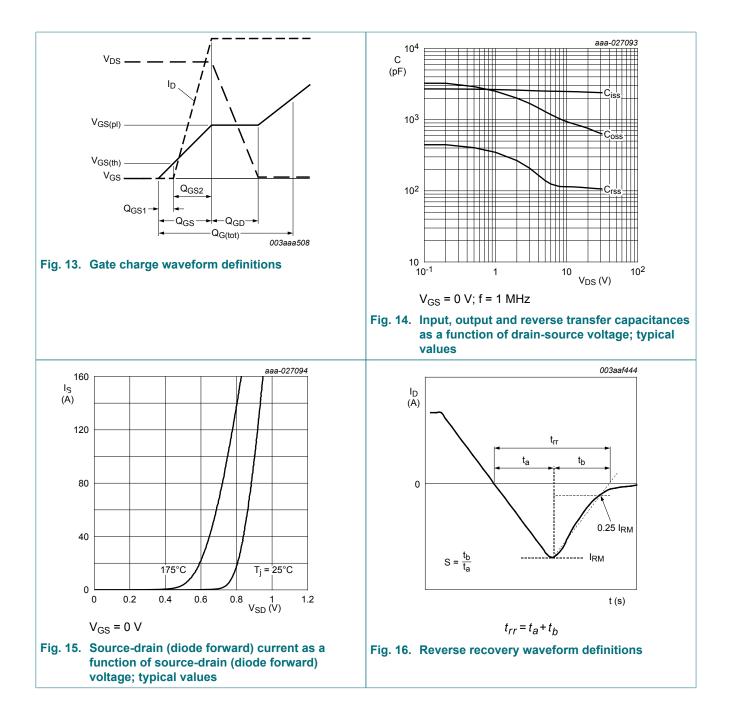
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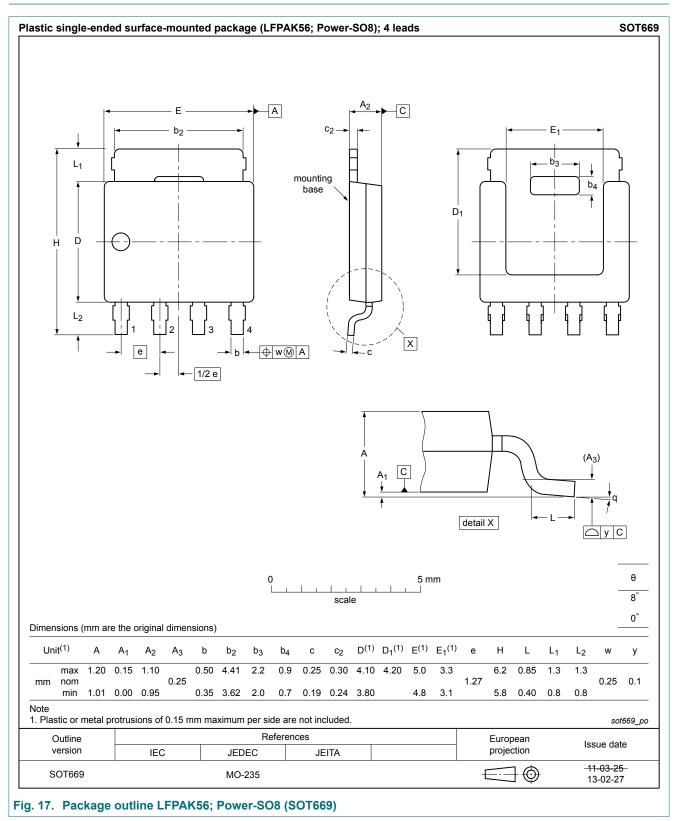


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11. Package outline



BUK7Y3R0-40H

N-channel 40 V, 3.0 m Ω standard level MOSFET in LFPAK56

12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

- [2] The term 'short data sheet' is explained in section "Definitions".
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